

Title (en)

INDIUM ANTIMONIDE (InSb) PHOTODETECTOR DEVICE AND STRUCTURE FOR INFRARED, VISIBLE AND ULTRAVIOLET RADIATION.

Title (de)

INSB-PHOTODETEKTOR UND STRUKTUR FÜR INFRAROT-, LICHT UND ULTRAVIOLETTSTRAHLUNG.

Title (fr)

DISPOSITIF ET STRUCTURE PHOTODETECTEURS A L'ANTIMONIURE D'INDIUM (InSb) POUR LES RAYONNEMENTS INFRAROUGE, VISIBLE ET ULTRAVIOLET.

Publication

EP 0653106 A1 19950517 (EN)

Application

EP 94919282 A 19940527

Priority

- US 9406038 W 19940527
- US 6889793 A 19930528

Abstract (en)

[origin: WO9428587A1] The light receiving or back-side surface (22) of an indium antimonide (InSb) photodetector device (10) substrate (12) is cleaned to remove all native oxides of indium and antimony therefrom. A passivation layer (26) is then formed on the surface (22) of a material such as silicon dioxide, silicon suboxide and/or silicon nitride which does not react with InSb to form a structure which would have carrier traps therein and cause flashing. The device (10) is capable of detecting radiation over a continuous spectral range including the infrared, visible and ultraviolet regions.

IPC 1-7

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IPC 8 full level

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CPC (source: EP)

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